

**CMOS Analog Switch**

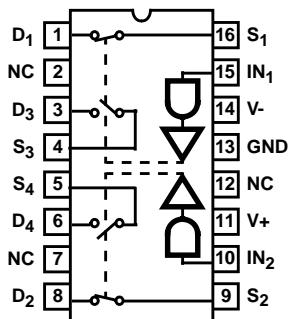
The HI-390 switch is a monolithic device fabricated using CMOS technology and the Intersil dielectric isolation process. This device is TTL compatible and features low leakage and supply currents, low and nearly constant ON resistance over the analog signal range, break-before-make switching and low power dissipation.

**Ordering Information**

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
HI1-0390-2	-55 to 125	16 Ld CERDIP	F16.3
HI3-0390-5	0 to 75	16 Ld PDIP	E16.3

**Pinout** Switch States shown for a Logic "1" Input

**DUAL SPDT HI-390 (CERDIP, PDIP)**  
TOP VIEW



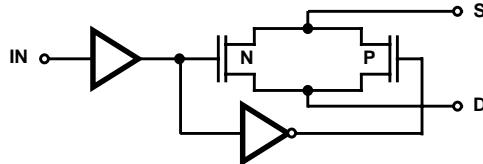
LOGIC	SW1, SW2	SW3, SW4
0	OFF	ON
1	ON	OFF

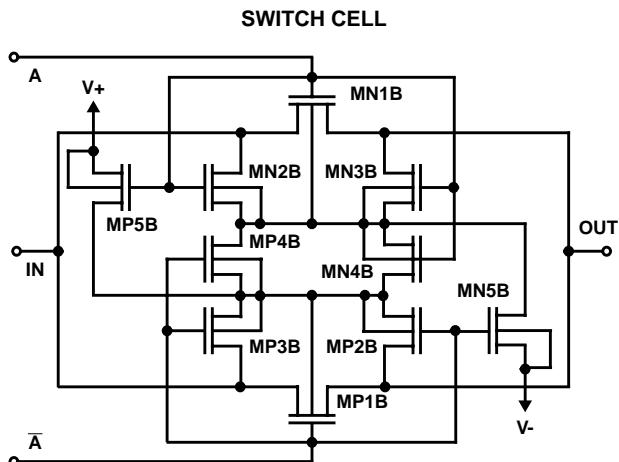
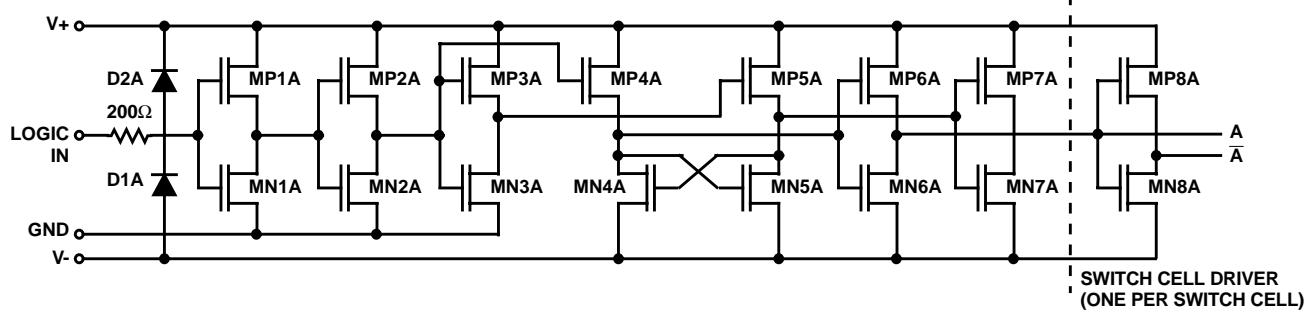
**Features**

- Analog Signal Range ( $\pm 15V$  Supplies) . . . . .  $\pm 15V$
- Low Leakage . . . . .  $40pA$
- Low On Resistance . . . . .  $35\Omega$
- Break-Before-Make Delay . . . . .  $60ns$
- Charge Injection . . . . .  $30pC$
- TTL Compatible
- Symmetrical Switch Elements
- Low Operating Power . . . . .  $1.0mW$

**Applications**

- Sample and Hold (i.e., Low Leakage Switching)
- Op Amp Gain Switching (i.e., Low On Resistance)
- Portable, Battery Operated Circuits
- Low Level Switching Circuits
- Dual or Single Supply Systems

**Functional Diagram**

**Schematic Diagrams****DIGITAL INPUT BUFFER AND LEVEL SHIFTER**

**Absolute Maximum Ratings**

Voltage Between Supplies (V+ to V-)	44V
Digital Input Voltage	(V+) +4V to (V-) -4V
Analog Input Voltage	(V+) +1.5V to (V-) -1.5V

**Operating Conditions**

Temperature Ranges	
HI-390-2	-55°C to 125°C
HI-390-5	0°C to 75°C

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

## NOTE:

1.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

**Electrical Specifications**      Supplies = +15V, -15V;  $V_{IN}$  = Logic Input.  $V_{IN}$  for Logic "1" = 4V, for Logic "0" = 0.8V,  
Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	-2			-5			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
<b>DYNAMIC CHARACTERISTICS</b>									
Switch ON Time, $t_{ON}$		25	-	210	300	-	210	300	ns
Switch OFF Time, $t_{OFF}$		25	-	160	250	-	160	250	ns
Break-Before-Make Delay, $t_{OPEN}$		25	-	60	-	-	60	-	ns
Charge Injection Voltage, $\Delta V$	(Note 7)	25	-	3	-	-	3	-	mV
OFF Isolation	(Note 6)	25	-	60	-	-	60	-	dB
Input Switch Capacitance, $C_S(OFF)$		25	-	16	-	-	16	-	pF
Output Switch Capacitance, $C_D(OFF)$		25	-	14	-	-	14	-	pF
Output Switch Capacitance, $C_D(ON)$		25	-	35	-	-	35	-	pF
Digital Input Capacitance, $C_{IN}$		25	-	5	-	-	5	-	pF
<b>DIGITAL INPUT CHARACTERISTICS</b>									
Input Low Level, $V_{INL}$		Full	-	-	0.8	-	-	0.8	V
Input High Level, $V_{INH}$		Full	4	-	-	4	-	-	V
Input Leakage Current (Low), $I_{INL}$	(Note 5)	Full	-	-	1	-	-	1	µA
Input Leakage Current (High), $I_{INH}$	(Note 5)	Full	-	-	1	-	-	1	µA
<b>ANALOG SWITCH CHARACTERISTICS</b>									
Analog Signal Range		Full	-15	-	+15	-15	-	+15	V
ON Resistance, $r_{ON}$	(Note 2)	25	-	35	50	-	35	50	Ω
		Full	-	40	75	-	45	75	Ω
OFF Input Leakage Current, $I_{S(OFF)}$	(Note 3)	25	-	0.04	1	-	0.04	5	nA
		Full	-	1	100	-	0.2	100	nA
OFF Output Leakage Current, $I_{D(OFF)}$	(Note 3)	25	-	0.04	1	-	0.04	5	nA
		Full	-	1	100	-	0.2	100	nA
ON Input Leakage Current, $I_{S(ON)}$	(Note 4)	25	-	0.03	1	-	0.03	5	nA
		Full	-	0.5	100	-	0.2	100	nA

**Electrical Specifications** Supplies = +15V, -15V;  $V_{IN}$  = Logic Input.  $V_{IN}$  for Logic "1" = 4V, for Logic "0" = 0.8V, Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	-2			-5			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
<b>POWER SUPPLY CHARACTERISTICS</b>									
Current, $I_+$	(Note 8)	25	-	0.09	0.5	-	0.09	0.5	mA
		Full	-	-	1	-	-	1	mA
Current, $I_-$	(Note 8)	25	-	0.01	10	-	0.01	100	μA
		Full	-	-	100	-	-	-	μA
Current, $I_+$	(Note 9)	25	-	0.01	10	-	0.01	100	μA
		Full	-	-	100	-	-	-	μA
Current, $I_-$	(Note 9)	25	-	0.01	10	-	0.01	100	μA
		Full	-	-	100	-	-	-	μA

## NOTES:

2.  $V_S = \pm 10V$ ,  $I_{OUT} = \pm 10mA$ . On resistance derived from the voltage measured across the switch under these conditions.
3.  $V_S = \pm 14V$ ,  $V_D = \pm 14V$ .
4.  $V_S = V_D = \pm 14V$ .
5. The digital inputs are diode protected MOS gates and typical leakages of 1nA or less can be expected.
6.  $V_S = 1V_{RMS}$ ,  $f = 500kHz$ ,  $C_L = 15pF$ ,  $R_L = 1K$ ,  $C_L = C_{FIXTURE} + C_{PROBE}$ , OFF Isolation =  $20 \log V_S/V_D$ .
7.  $V_S = 0V$ ,  $C_L = 10nF$ , Logic Drive = 5V pulse. Switches are symmetrical; S and D may be interchanged. Charge Injection =  $Q = C_L \times \Delta V$ .
8.  $V_{IN} = 4V$  (one input, all other inputs = 0V).
9.  $V_{IN} = 0.8V$  (all inputs).

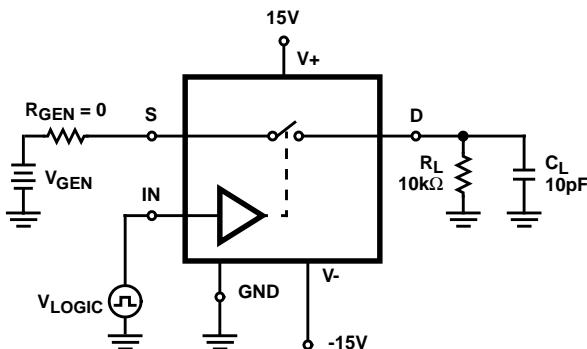
**Test Circuits and Waveforms**

FIGURE 1A. TEST CIRCUIT

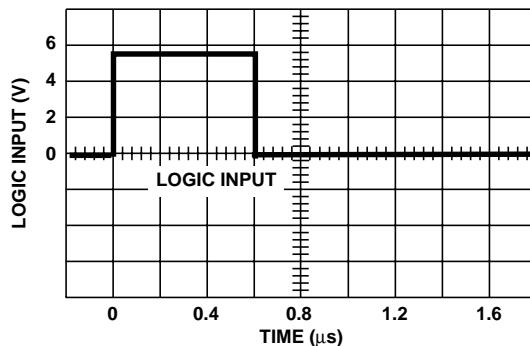
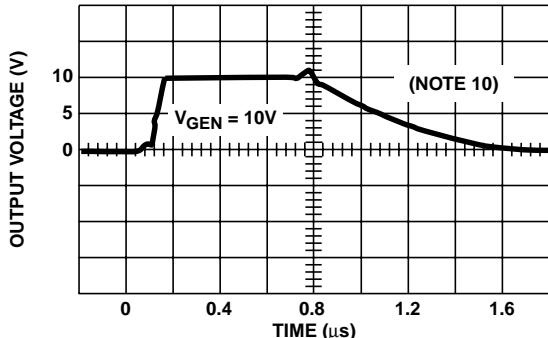
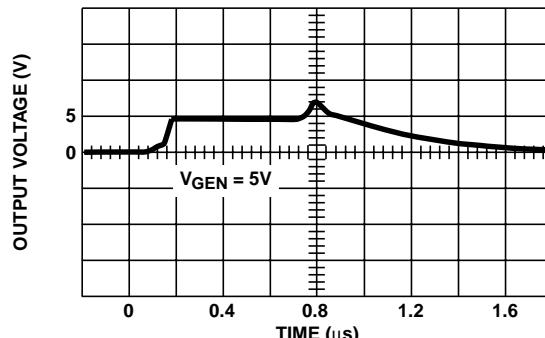
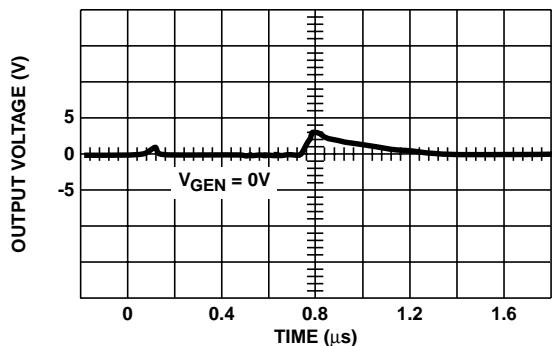
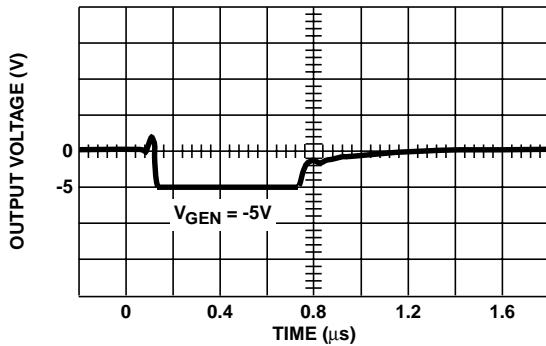
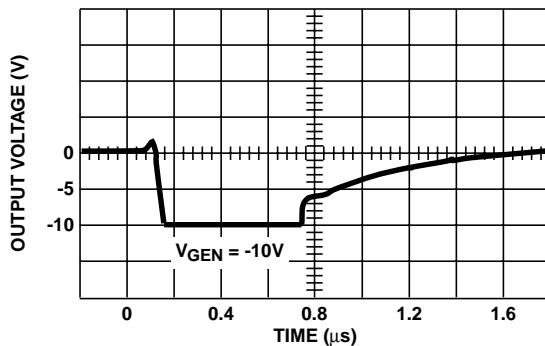


FIGURE 1B. LOGIC INPUT

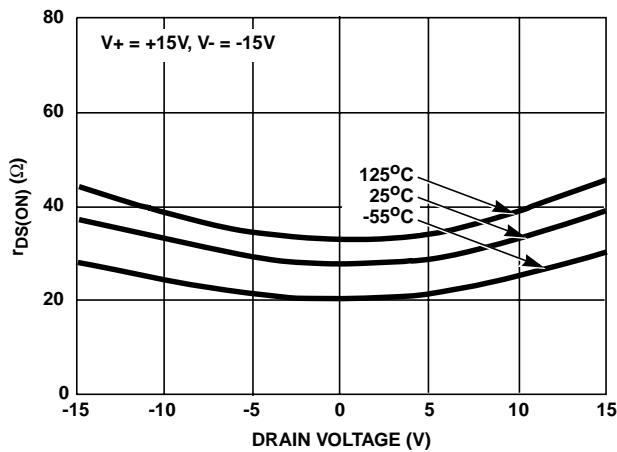
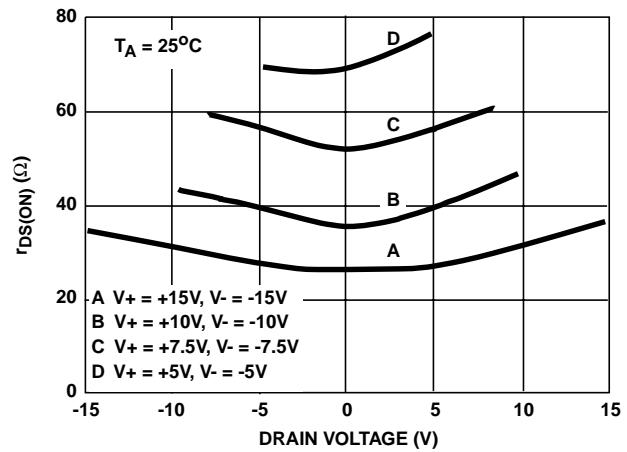
FIGURE 1C.  $V_{ANALOG} = 10V$ FIGURE 1D.  $V_{ANALOG} = 5V$

***Test Circuits and Waveforms (Continued)***FIGURE 1E.  $V_{ANALOG} = 0V$ FIGURE 1F.  $V_{ANALOG} = -5V$ FIGURE 1G.  $V_{ANALOG} = -10V$ 

NOTE:

10. If  $R_{GEN}$ ,  $R_L$  or  $C_L$  is increased, there will be proportional increases in rise and/or fall RC times.

FIGURE 1. SWITCHING WAVEFORMS FOR VARIOUS ANALOG INPUT VOLTAGES

***Typical Performance Curves***FIGURE 2.  $r_{DS(ON)}$  vs  $V_D$ FIGURE 3.  $r_{DS(ON)}$  vs  $V_D$

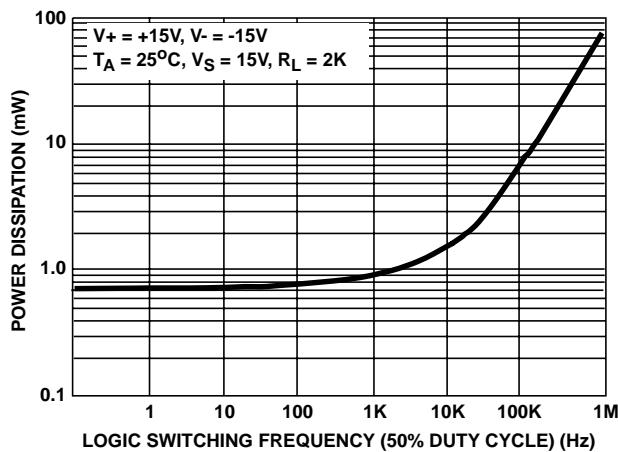
**Typical Performance Curves (Continued)**

FIGURE 4. DEVICE POWER DISSIPATION vs SWITCHING FREQUENCY (SINGLE LOGIC INPUT)

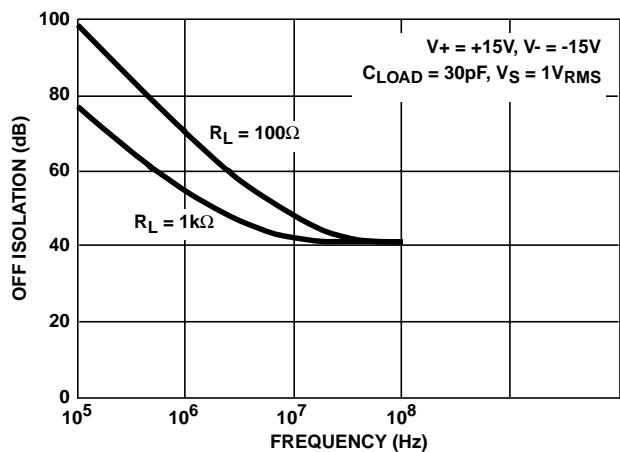
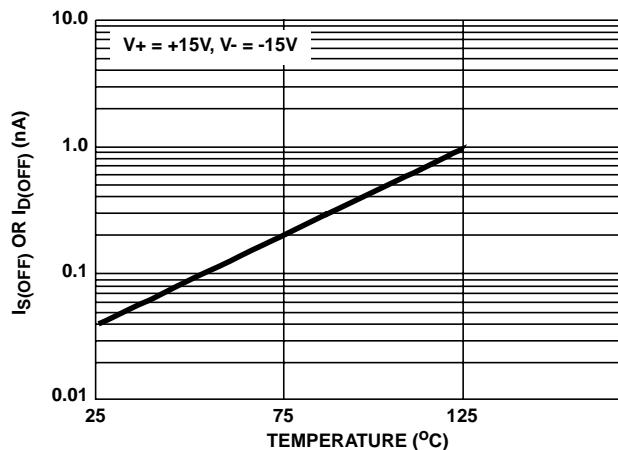
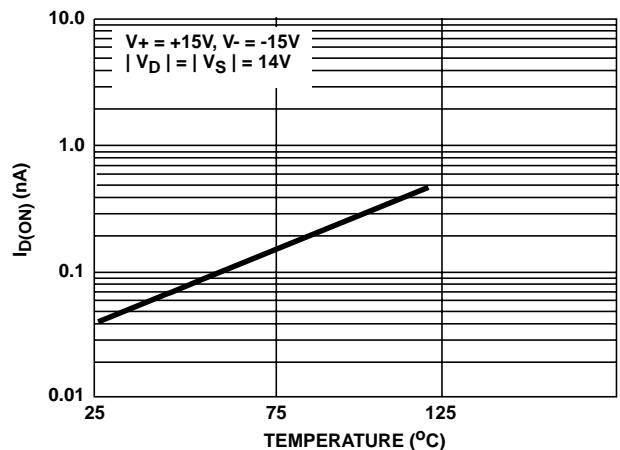


FIGURE 5. OFF ISOLATION vs FREQUENCY

FIGURE 6.  $I_S(\text{OFF})$  OR  $I_D(\text{OFF})$  vs TEMPERATURE (NOTE 11)FIGURE 7.  $I_D(\text{ON})$  vs TEMPERATURE (NOTE 11)

NOTE:

11. The net leakage into the source or drain is the N-Channel leakage minus the P-Channel leakage. This difference can be positive, negative or zero depending on the analog voltage and temperature, and will vary greatly from unit to unit.

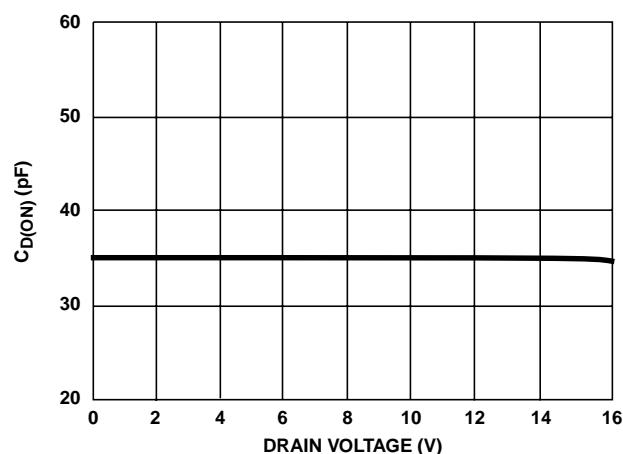


FIGURE 8. OUTPUT ON CAPACITANCE vs DRAIN VOLTAGE

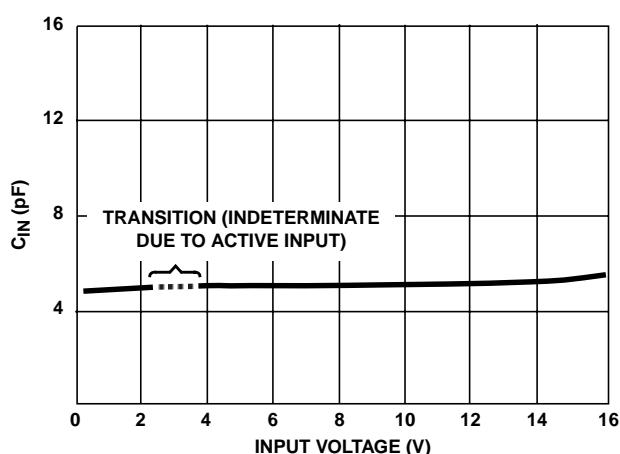


FIGURE 9. DIGITAL INPUT CAPACITANCE vs INPUT VOLTAGE

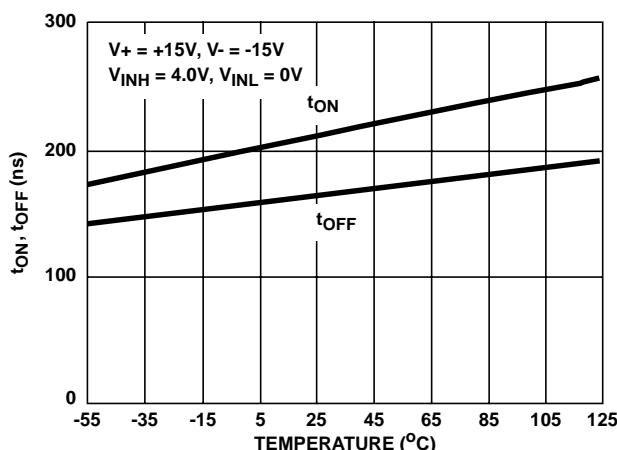
**Typical Performance Curves (Continued)**

FIGURE 10. SWITCHING TIME vs TEMPERATURE

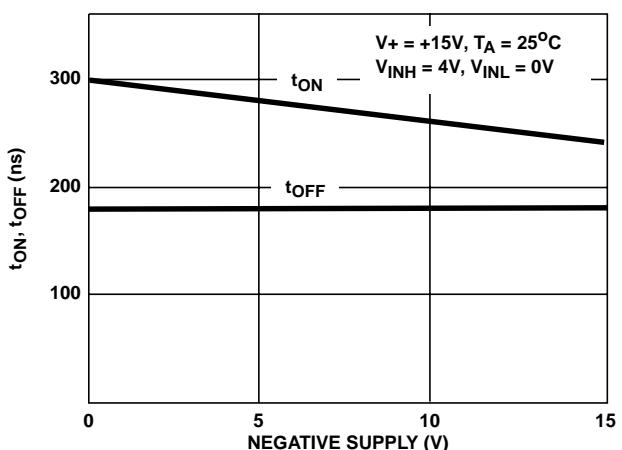


FIGURE 11. SWITCHING TIME vs NEGATIVE SUPPLY VOLTAGE

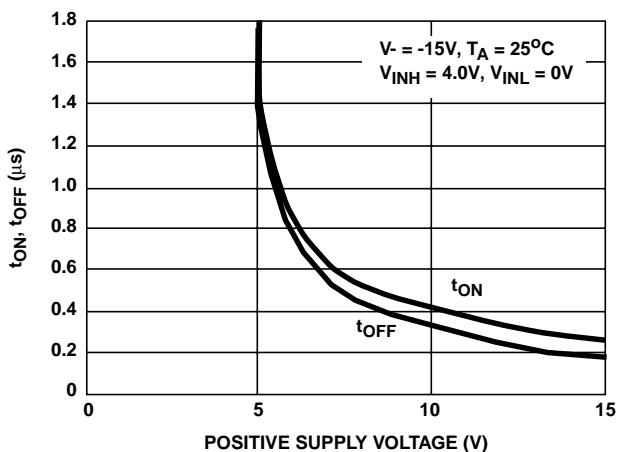


FIGURE 12. SWITCHING TIME vs POSITIVE SUPPLY VOLTAGE

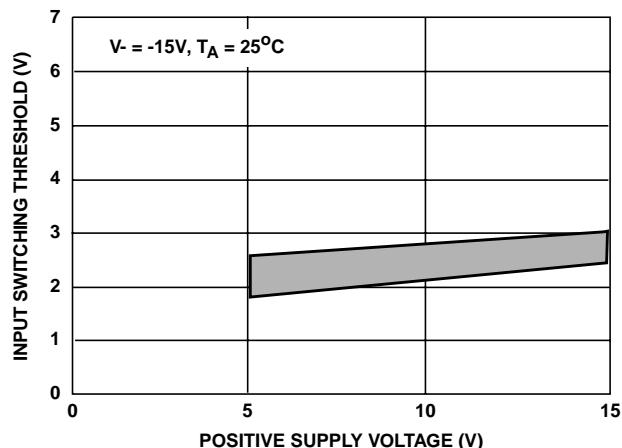


FIGURE 13. INPUT SWITCHING THRESHOLD vs POSITIVE SUPPLY VOLTAGE

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